

**S1C17 M01/W22/W23/W15**  
Self-Modifying  
Software (FLS)  
Manual

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## Summary

This material is intended to provide reference materials for application programs to self-modify internal flash memory by using the FLS17 M01/W22/W23/W15 library, the erasing/writing software of flash memory embedded in S1C17M01/W22/W23/W15.

## Operating Environment

- PC
  - GNU17 (S5U1C17001C) development tool installed\*
  - ICDmini USB driver installed
- ICDmini (S5U1C17001H2, S5U1C17001H3)
  - The USB cable is necessary for connecting to PC.
- Target system (user target board or our company's evaluation board)
- S1C17xxx self-modifying software package (this package)

## Precautions for Usage

The library which comes with this package is only a sample. Our company does not take any responsibility for any problems caused by this library. You should fully verify the behavior of the product.

This material is common to S1C17M01/W22/W23/W15.

In this material, "xxx" of S1C17 (xxx) represents the concerned model name of M01/W22/W23/W15.

To supply power from outside, fully take time until the power supply becomes stable.

When the operation is finished, stop the power supply from outside

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## 1. Overview

The self-modifying software package provides a library to rewrite program codes and data in the flash memory embedded in target models. The function calls from an application program can implement the operations to erase and write flash memory by linking this library with the application program.

When the function calls from the application program erase and write the flash memory, ICDmini (S5U1C17001H2, S5U1C17001H3) becomes unnecessary.

Note: ICDmini is used for debugging and writing an initial program.

### 1.1 Function

This section describes the functions to be provided by the library.

Flash memory erase function:

```
flash_erase(char * flsTopAdd, unsigned short startSct, unsigned short endSct)
```

The sectors of the flash memory embedded in S1C17 (xxx) are erased by specifying the start address of the flash memory, and start and end sectors to be erased.

The sectors to be erased can be 1 to 16 for M01, 1 to 32 for W22/W15, and 1 to 48 for W23.

Flash memory write function:

```
flash_load(char * loadAdd, unsigned short loadSize, unsigned char* pData)
```

The data in the memory is written into the flash memory by specifying the start destination address, data size, and pointer to data to be written.

Note: The scope of the data to be written is not checked in the library.

#### <Points to note on this package>

1. This package is created for developing programs in GNU17 (S5U1C17001C).
2. The verify function is incorporated in the flash memory erase/write functions.

### 1.2 Folder Configuration

This section describes the folder configuration of this package:

```
+ s1c17(xxx)self_r1x
  + lib : Self-modifying library
  + c17(xxx)_sample_gnu17v2 : Sample program for GNU17 Ver.2.x
  + c17(xxx)_sample_gnu17v3 : Sample program for GNU17 Ver.3.x
  - s1c17m01_w22_w23_w15flsan_i_revXXX.pdf : Manual (Japanese)
  - s1c17m01_w22_w23_w15flsan_e_revXXX.pdf : Manual (English)
  - s1c17(xxx)self_notes_j.txt : Notes for each MCU model (Japanese)
  - s1c17(xxx)self_notes_e.txt : Notes for each MCU model (English)
  - License_e.txt : Software license agreement (English)
```

### 1.3 File Configuration

The table below lists the library file configuration.

Table 1 s1c17(xxx)self\_r1x /lib

Filename	Function
fls17(xxx)RAM.o	Erases/writes the flash memory of S1C17 (xxx)
fls17(xxx)ROM.o	Erases/writes the flash memory of S1C17 (xxx)
fl_self.h	Header file for declaring functions

The table below lists the file configuration of sample program.

## 1. Overview

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Table 2 c17(xxx)\_sample

File/folder name	Function
Lib	Self-modifying library (folder)
boot.c	boot program
main.c	main program
data.c	Data (before update)
update.c	Data for update

## 2. How to Use Library

This chapter describes necessary information and precautions for using this library. This chapter also describes a sample program using this library.

### 2.1 How to Use Library in Application Program

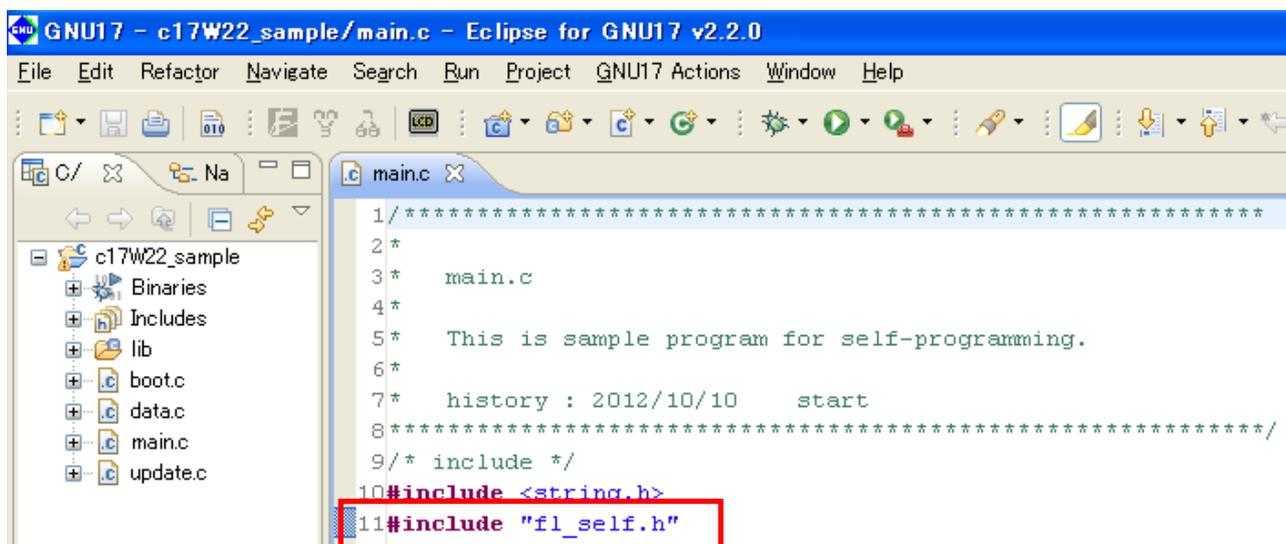
This section describes necessary information for using this library in the source files of application programs.

In addition, for information on how to incorporate the library into a project of application program, refer to Appendix B. How to Incorporate Library into Project.

#### 1. Declaration of Header File

Declare to include "fl\_self.h" in a source file using this library.

Note: If an include path is not set, specify the path before the inclusion.



#### 2. Adding Flash Memory Erase/Write functions

Add the functions of this library to erase/write flash memory to the source code of the application program.

For the function specification, refer to 3. Library Specification.

```
int update(void) {
    int result;

    // erase 0xB000-0xBFFF
    result = flash_erase((char *)0x8000, 7, 7);

    if(result == FLS_E_SUCCESS) {
        // write data to 0xb000
        result = flash_load((char *)0xB000, 16, updateLineBit);
    }

    return result;
}
```

### 2.2 Flash Programming Voltage VPP

When erasing/writing flash memory, supply the Flash programming power (VPP power).

The procedures to supply VPP power are as follows. In addition, stop the VPP power supply other than when erasing/writing flash memory.

## 2. How to Use Library

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- ① Check to see that VDD is not less than 1.8V.
- ② Put the desired data in RAM.
- ③ Supply the VPP power.
- ④ Wait until the VPP voltage becomes stable.
- ⑤ Execute the flash\_erase function to erase specified area.
- ⑥ Execute the flash\_load function to write data into the specified address in erased area.
- ⑦ To write data into another address in erased area, repeat step ⑥.
- ⑧ Stop the VPP power.

Refer to "S1C17 (xxx) Technical Manual" for Flash programming voltage and basic external connection diagram.

### 2.3 Internal RAM Usage

This library uses internal RAM area.

Please refer Notes for each MCU model "s1c17(xxx)self\_notes\_e.txt" to know internal RAM usage.

### 2.4 Precautions for Using Library

When using this library, be careful about the followings:

- Disable interrupts before the flash\_erase and flash\_load functions.
- Do not destruct the area where the library is laid out while executing library.
- When using this library, be aware of rewritable count of flash memory. For information about flash memory specification, refer to "S1C17 (xxx) Technical Manual."
- This library works as follows:
  1. The library uses 16bit timer (T16), ch. 0. **Therefore, the register of 16bit timer, ch.0 is changed. Be aware when a program uses both the 16bit timer and this library.**
  2. In W22/W23/W15, VD1 is changed to 1.8V while rewriting flash memory. After rewriting flash memory, VD1 is reverted back to 1.4V. When using this library, make sure to stop all peripheral circuits set by the customer.
  3. The system clock is changed to: IOSC for M01, OSC3 for W22/W23/W15.
  4. **In W22/W23/W15, this library reverts CGL OSC3 Control Register of clock generator (CLG) back to initial value. Therefore, CLG OSC3 Control Register is changed. Be aware when a program uses both CLG OSC3 Control Register and this library.**

### 2.5 Sample Program

#### 1. Sample Program Specification

The sample program performs the following operation using this library.

- Erase a sector in the address 0xB000 area and then write 16byte of data.

#### 2. Preparation

To run the sample program in IDE, refer to the procedures below. Also, when using the library, keep in mind the items described in the sections 2.1 to 2.4 above.

- ① Import a project  
Launch IDE and import the sample program.
- ② Build  
Use IDE to build the sample program.
- ③ Connect  
Connect ICDmini and target system to PC.
- ④ Unlock Flash security  
To debug the sample program with IC supporting the Flash security, unlock the Flash security.
- ⑤ Load program  
Use IDE to load the sample program.

- ⑥ Supply VPP power  
Supply VPP power.
- ⑦ Run  
Reset the target system to run the program.

For more information, refer to "S1C17 (xxx) Technical Manual," "S5U1C17001C Manual," and "S5U1C17001H User Manual (ICDmini)."

### 3. Operations Overview

- ① Erase the sector 7 (0xB000 to 0xB7FF) in internal flash memory (main.c/flash\_erase).
  - Start address of flash memory: 0x8000
  - Erase start sector of flash memory: 7
  - Erase end sector of flash memory: 7
- ② Write the update data updateLineBit[] into the erased sector 0xB000 (main.c/flash\_load).
  - Write destination address: 0xB000
  - Write data size: 16byte
  - Pointer to writing data: updateLineBit

The data starting 0xB000 is as follows before and after the rewriting.

Before the rewriting (0xB000)

00 01 02 03 04 05 06 07 08 09 0A 0B 0C 0D 0E 0F
---

After the rewriting (0xB000)

0F 0E 0D 0C 0B 0A 09 08 07 06 05 04 03 02 01 00
---

Confirm the rewritten result by the memory dump.

For information on the sector numbers and corresponding addresses, refer to Appendix A. Flash Memory Specification.

For information about flash\_erase, flash\_load functions, refer to 3.1 Flash Memory Erase/Write Function Details.

### 3. Library Specification

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## 3. Library Specification

### 3.1 Flash Memory Erase/Write Function Details

This section describes the functions described in fl\_17(xxx).o (fl\_17(xxx).c).

#### Erase flash memory

<b>Function Name</b>		
flash_erase(char * flsTopAdd, unsigned short startSct, unsigned short endSct)		
<b>Argument</b>		
flsTopAdd	unsigned long	Represents the start address of flash memory.
startSct	unsigned long	Represents the erase start address of flash memory.
endSct	unsigned long	Represents the erase end address of flash memory.
<b>Return Value</b>		
int		Represents the erase result (error code) of flash memory.
<b>Function</b>		
Erase the flash memory according to the parameter specified by arguments. ① Check whether the arguments are correct. ② Erase the memory. ③ Return a return value.		
<b>Remarks</b>		
The scope of sector numbers specified by second and third arguments: 1 to 16 for M01, 1 to 32 for W22/W15, and 1 to 48 for W23.		

#### Write flash memory

<b>Function Name</b>		
flash_load(char * loadAdd, unsigned short loadSize, unsigned char* pData)		
<b>Argument</b>		
loadAdd	unsigned long	Represents the write destination address.
loadSize	unsigned long	Represents the write data size.
pData	unsigned char*	Represents a pointer to the write data. The pointer should point the RAM space.
<b>Return Value</b>		
int		Represents the write result (error code) of flash memory.
<b>Function</b>		
Write data into the flash memory according to the parameter specified by arguments. ① Convert virtual address into physical address. ② Write data. - Initialize the setting. - Check whether the desired data and the data in the destination area match each other. - If they do not match each other, write data. ③ Return a return value.		
<b>Remarks</b>		
The write data unit is "byte (8bit)."		

### 3.2 Error Code Definition

Table 3 Error Code

Definition Name	Value	Description
FLS_E_SUCCESS	0	The flash operation ended successfully
FLS_E_PROGRAM_COUNT_OVER_ERR	1	Program count error Returns if the verify count exceeds the maximum program count by verifying data during the writing/erasing (compare the data with desired data during writing and 0xFFFF during erasing).

### 3. Library Specification

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FLS_E_STRAT_SCT_ERR	3	The erase start sector is out of scope Returns if the erase start sector is less than zero or exceeds the maximum sector number.
FLS_E_END_SCT_ERR	4	The erase end sector is out of scope Returns if the erase end sector is less than zero or exceeds the maximum sector number.
FLS_E_TOP_ADDRESS_ERR	5	Start address error Returns if the first argument (start address of flash memory) of the FLASH_ERASE function is not equal to the start address value of flash memory.

## Appendix

### A. Flash Memory Specification

This section describes internal flash memory specification of each model. For information about internal flash memory, refer to "S1C17 (xxx) Technical Manual."

#### 1. S1C17M01 Internal Flash Memory Configuration

- Sector number : 16sectors
- Memory size : 32Kbyte
- Erase unit : Sector (2Kbyte)
- Write unit : Byte (8bit)
- Write time : Initial sector programming time: 109msec (typical)  
Initial sector erase time: 121msec (typical)
- Flash programming voltage (V<sub>PP</sub>) : erase: 7.5V, write: 7.5V  
To supply power from outside, fully take time until the power supply becomes stable.

When the operation is finished, stop the power supply from outside.

Table 4 Correspondence between S1C17M01 Memory Address and Flash Sector

S1C17M01 Address	Flash Sector Number
0x0f800 to 0x0fff	16
0x0f000 to 0x0f7ff	15
0x0e800 to 0x0efff	14
0x0e000 to 0x0e7ff	13
0x0d800 to 0x0dff	12
0x0d000 to 0x0d7ff	11
0x0c800 to 0x0cff	10
0x0c000 to 0x0c7ff	9
0x0b800 to 0x0bfff	8
0x0b000 to 0x0b7ff	7
0x0a800 to 0x0aff	6
0x0a000 to 0x0a7ff	5
0x09800 to 0x09fff	4
0x09000 to 0x097ff	3
0x08800 to 0x08fff	2
0x08000 to 0x087ff	1

## 2. S1C17W22 Internal Flash Memory Configuration

- Sector number : 32sectors
- Memory size : 64Kbyte
- Erase unit : Sector (2Kbyte)
- Write unit : Byte (8bit)
- Write time : Initial sector programming time: 220msec (typical)  
Initial sector erase time: 208msec (typical)
- Flash programming voltage (V<sub>PP</sub>) : erase: 7.5V, write: 7.5V  
To supply power from outside, fully take time until the power supply becomes stable.

When the operation is finished, stop the power supply from outside.

Table 5 Correspondence between S1C17W22 Memory Address and Flash Sector

S1C17W22 Address	Flash Sector Number
0x17800 to 0x17fff	32
0x17000 to 0x177ff	31
0x16800 to 0x16fff	30
0x16000 to 0x167ff	29
0x15800 to 0x15fff	28
0x15000 to 0x157ff	27
0x14800 to 0x14fff	26
0x14000 to 0x147ff	25
0x13800 to 0x13fff	24
0x13000 to 0x137ff	23
0x12800 to 0x12fff	22
0x12000 to 0x127ff	21
0x11800 to 0x11fff	20
0x11000 to 0x117ff	19
0x10800 to 0x10fff	18
0x10000 to 0x107ff	17
0x0f800 to 0x0ffff	16
0x0f000 to 0x0f7ff	15
0x0e800 to 0x0efff	14
0x0e000 to 0x0e7ff	13
0x0d800 to 0x0dfff	12
0x0d000 to 0x0d7ff	11
0x0c800 to 0x0cfff	10
0x0c000 to 0x0c7ff	9
0x0b800 to 0x0bfff	8
0x0b000 to 0x0b7ff	7
0x0a800 to 0x0afff	6
0x0a000 to 0x0a7ff	5
0x09800 to 0x09fff	4
0x09000 to 0x097ff	3
0x08800 to 0x08fff	2
0x08000 to 0x087ff	1

### 3. S1C17W23 Internal Flash Memory Configuration

- Sector number : 48sectors
- Memory size : 96Kbyte
- Erase unit : Sector (2Kbyte)
- Write unit : Byte (8bit)
  
- Write time : Initial sector programming time: 220msec (typical)  
Initial sector erase time: 208msec (typical)
- Flash programming voltage (V<sub>PP</sub>) : erase: 7.5V, write: 7.5V  
To supply power from outside, fully take time until the power supply becomes stable.

When the operation is finished, stop the power supply from outside.

Table 6 Correspondence between S1C17W23 Memory Address and Flash Sector

S1C17W23 Address	Flash Sector Number	S1C17W23 Address	Flash Sector Number
0x17800 to 0x17fff	32	0x1f800 to 0x1ffff	48
0x17000 to 0x177ff	31	0x1f000 to 0x1f7ff	47
0x16800 to 0x16fff	30	0x1e800 to 0x1efff	46
0x16000 to 0x167ff	29	0x1e000 to 0x1e7ff	45
0x15800 to 0x15fff	28	0x1d800 to 0x1dfff	44
0x15000 to 0x157ff	27	0x1d000 to 0x1d7ff	43
0x14800 to 0x14fff	26	0x1c800 to 0x1cfff	42
0x14000 to 0x147ff	25	0x1c000 to 0x1c7ff	41
0x13800 to 0x13fff	24	0x1b800 to 0x1bfff	40
0x13000 to 0x137ff	23	0x1b000 to 0x1b7ff	39
0x12800 to 0x12fff	22	0x1a800 to 0x1afff	38
0x12000 to 0x127ff	21	0x1a000 to 0x1a7ff	37
0x11800 to 0x11fff	20	0x19800 to 0x19fff	36
0x11000 to 0x117ff	19	0x19000 to 0x197ff	35
0x10800 to 0x10fff	18	0x18800 to 0x18fff	34
0x10000 to 0x107ff	17	0x18000 to 0x187ff	33
0x0f800 to 0x0ffff	16		
0x0f000 to 0x0f7ff	15		
0x0e800 to 0x0efff	14		
0x0e000 to 0x0e7ff	13		
0x0d800 to 0x0dfff	12		
0x0d000 to 0x0d7ff	11		
0x0c800 to 0x0cfff	10		
0x0c000 to 0x0c7ff	9		
0x0b800 to 0x0bfff	8		
0x0b000 to 0x0b7ff	7		
0x0a800 to 0x0afff	6		
0x0a000 to 0x0a7ff	5		
0x09800 to 0x09fff	4		
0x09000 to 0x097ff	3		
0x08800 to 0x08fff	2		
0x08000 to 0x087ff	1		

#### 4. S1C17W15 Internal Flash Memory Configuration

- Sector number : 32sectors
- Memory size : 64Kbyte
- Erase unit : Sector (2Kbyte)
- Write unit : Byte (8bit)
  
- Write time : Initial sector programming time: 220msec (typical)  
Initial sector erase time: 208msec (typical)
- Flash programming voltage (V<sub>PP</sub>) : erase: 7.5V, write: 7.5V  
To supply power from outside, fully take time until the power supply becomes stable.

When the operation is finished, stop the power supply from outside.

Table 7 Correspondence between S1C17W15 Memory Address and Flash Sector

S1C17W15 Address	Flash Sector Number
0x17800 to 0x17fff	32
0x17000 to 0x177ff	31
0x16800 to 0x16fff	30
0x16000 to 0x167ff	29
0x15800 to 0x15fff	28
0x15000 to 0x157ff	27
0x14800 to 0x14fff	26
0x14000 to 0x147ff	25
0x13800 to 0x13fff	24
0x13000 to 0x137ff	23
0x12800 to 0x12fff	22
0x12000 to 0x127ff	21
0x11800 to 0x11fff	20
0x11000 to 0x117ff	19
0x10800 to 0x10fff	18
0x10000 to 0x107ff	17
0x0f800 to 0x0ffff	16
0x0f000 to 0x0f7ff	15
0x0e800 to 0x0efff	14
0x0e000 to 0x0e7ff	13
0x0d800 to 0x0dfff	12
0x0d000 to 0x0d7ff	11
0x0c800 to 0x0cfff	10
0x0c000 to 0x0c7ff	9
0x0b800 to 0x0bfff	8
0x0b000 to 0x0b7ff	7
0x0a800 to 0x0afff	6
0x0a000 to 0x0a7ff	5
0x09800 to 0x09fff	4
0x09000 to 0x097ff	3
0x08800 to 0x08fff	2
0x08000 to 0x087ff	1

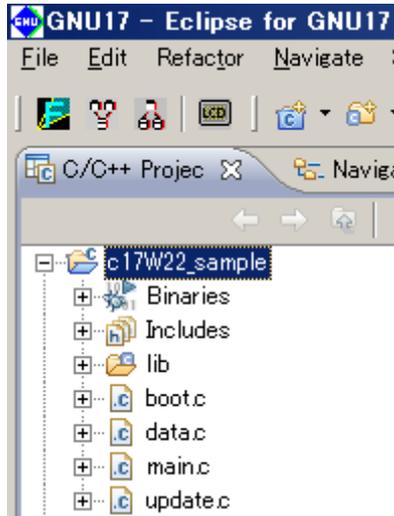
## B. How to Incorporate Library into Project (GNU17 Ver.2.x)

This section describes how to use the library in this package in GNU17 Ver.2.x.  
(Now, W22 is taken as an example)

For more information about how to use GNU17 Ver.2.x, refer to the compiler manual.

### 1. Adding Library and Header File

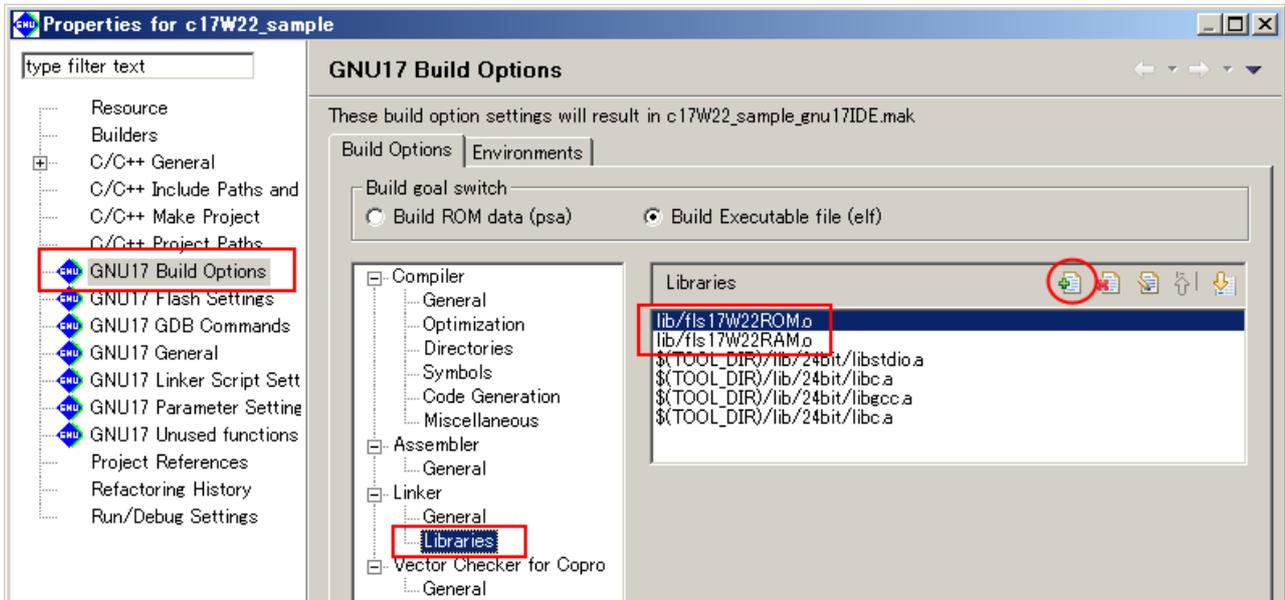
Import the lib folder in the package into the project folder.



### 2. Library Setting

In order to use the library imported, add the library setting.

Click [Properties]-[GNU17 Build Options]-[Linker]-[Libraries] of the project, click the button circled in red in the figure below, and select and add "fls17(xxx)ROM.o ", "fls17(xxx)RAM.o " in the lib folder.

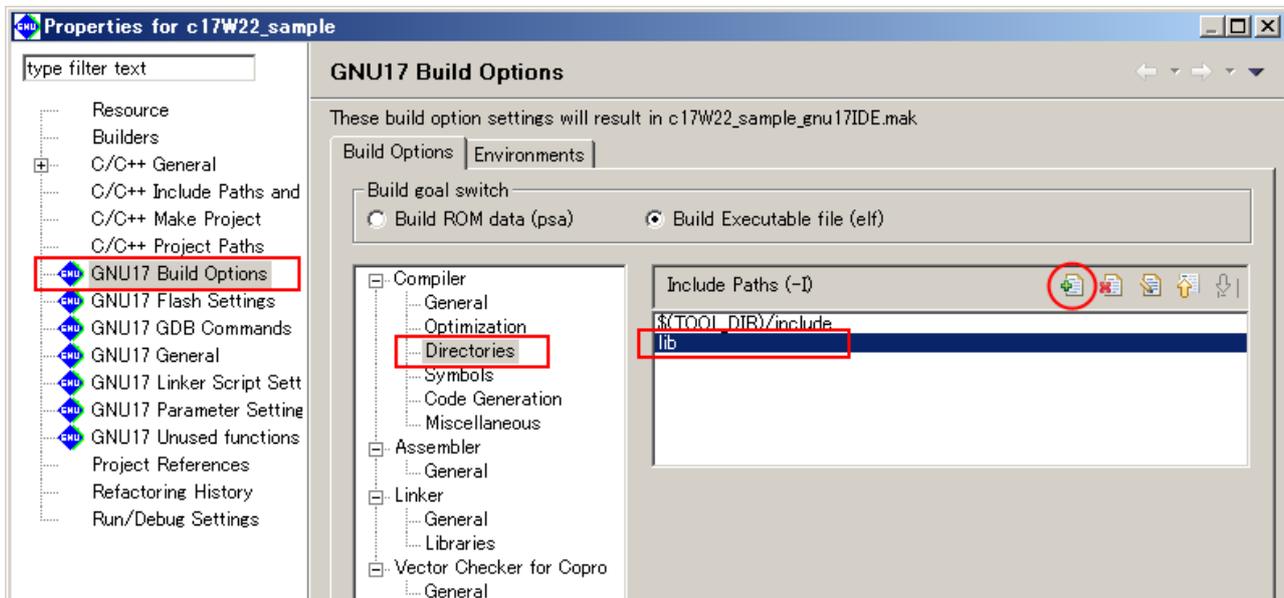


### 3. Include Path Setting

In order to use "fl\_self.h" in the lib folder, set the include path.

Click [Properties]-[GNU17 Build Options]-[Directories] of the project, click the button circled in red in the figure below, and set the include path for the lib folder.

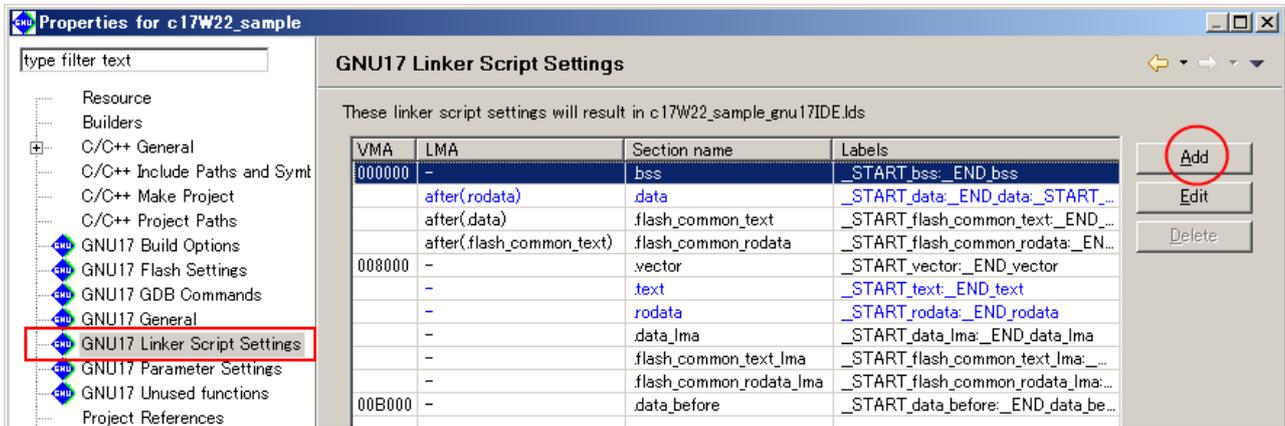
Note: This setting is not necessary if the include path is specified directly in the source file.



#### 4. Linker Script Setting

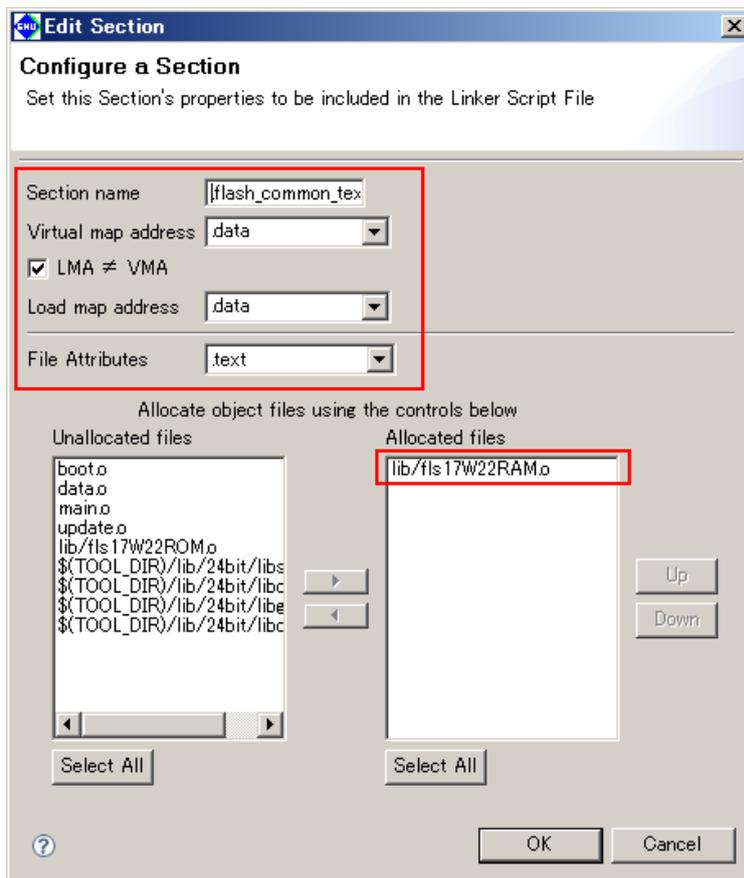
Set the linker script of the library imported.

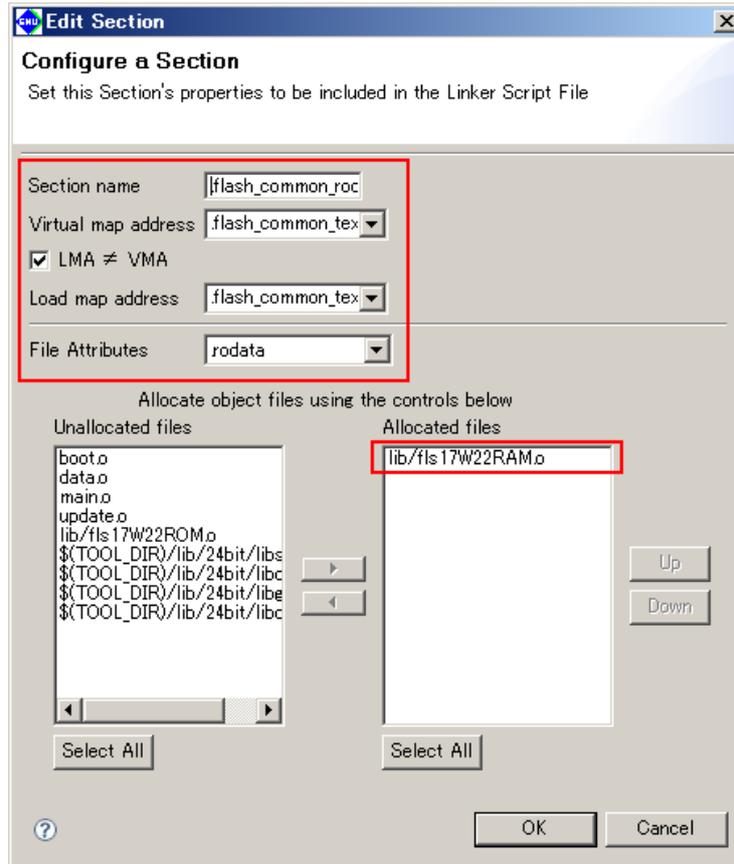
Click [Properties]-[GNU17 Linker Script Settings] of the project, click the button circled in red in the figure below, and add sections for the library layout.



Add the sections: `.flash_common_text` and `.flash_common_rodata`. Add the sections whose name begins with a dot (".") as written above, referring to figures below.

As shown in the figure below, allocate "fls1(xxx)RAM.o" to each section above. Since "fls17(xxx)RAM.o" is a library for issuing control commands to flash memory and need to be executed in internal RAM, allocate execution addresses (VMA) in internal RAM. Note that it is not necessary to allocate "fls17(xxx)ROM.o" in RAM.





## C. How to Incorporate Library into Project (GNU17 Ver.3.x)

This section describes how to use the library in this package in GNU17 Ver.3.x.

For more information about how to use GNU17 Ver.3.x, refer to the compiler manual.

### 1. Adding Library and Header File

Import the "lib" folder in the package into the project folder "src".

### 2. Library Setting

In order to use the library imported, add the library setting.

Select [Properties]-[C/C++ Build]-[Environment] of the project, and add "fls17(xxx) ROM.o", "fls17(xxx) RAM.o" in the "src\lib" folder to Value of Variable "GCC17\_USER\_LIBS".

```
..\src\lib\fls17(xxx)RAM.o;..\src\lib\fls17(xxx)ROM.o
```

### 3. Include Path Setting

In order to use "fl\_self.h" in the lib folder, set the include path.

Select [Properties]-[C/C++ Build]-[Settings]-[Tool Settings]-[Cross GCC Compiler]-[Includes] of the project, and set the include path for the "src\lib" folder.

```
"${workspace_loc}/${ProjName}/src/lib"
```

### 4. Linker Script Setting

Set the linker script of the library.

The example of linker script described for self modify internal flash exists in the following folder. Copy this script to the project folder.

```
\c17(xxx)_sample_gnu17v3\selfmodifying.x
```

Select [Properties]-[C/C++ Build]-[Settings]-[Tool Settings]-[Cross GCC Linker]-[Miscellaneous] of the project, and set the copied linker script file at [Other options].

```
-T ..\selfmodifying.x
```

In this linker script, the following symbols necessary for the operation of the library are defined, and the execution address of the library "fls17(xxx)RAM.o" is arranged in internal RAM.

```
__START_flash_common_text_lma
__START_flash_common_text
__END_flash_common_text
__START_flash_common_rodata_lma
__START_flash_common_rodata
__END_flash_common_rodata
```

Moreover, this script sets that "fls17(xxx) RAM.o" is not arranged in ROM by the following descriptions.

```
*(EXCLUDE_FILE (*fls17*RAM.o) .text)
*(EXCLUDE_FILE (*crt0.o *fls17*RAM.o) .rodata)
```

In this script, arrange the data to be rewritten to the ".updateable" section. When such a section is unnecessary, delete the ".updateable" section.



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